

1SS367

PRV : 15 Volts

Io : 100 mA

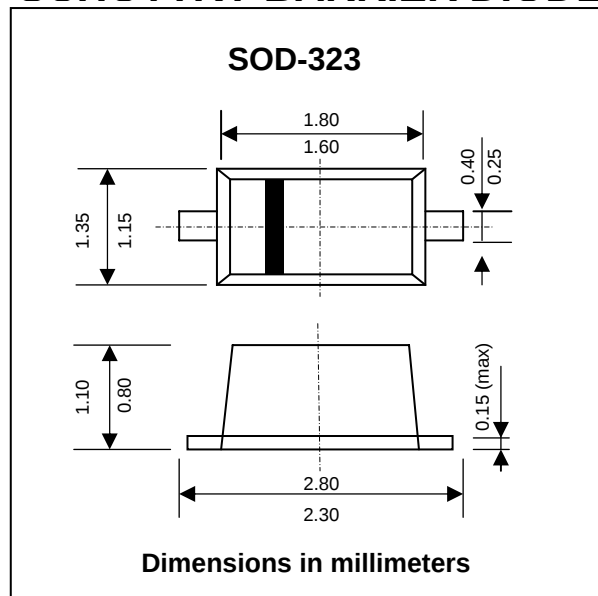
FEATURES :

- * Low forward voltage
- * High speed switching
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SOD-323 plastic Case
- * Weight : approx. 0.004 g

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE



ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	200	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	125	°C
Storage Temperature	T_{STG}	-55 to +125	°C
Operating Temperature Range	T_{opr}	-40 to +100	°C

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Test Condition	Symbol	Max.	Unit
Forward Voltage	$I_F = 5 \text{ mA}$	V_F	300	mV
	$I_F = 100 \text{ mA}$	V_F	500	mV
Reveres Current	$V_R = 10 \text{ V}$	I_R	20	μA
Total Capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	40	pF

RATINGS AND CHARACTERISTIC CURVES (1SS367)

FIG.1 - POWER DISSIPATION VS.
AMBIENT TEMPERATURE

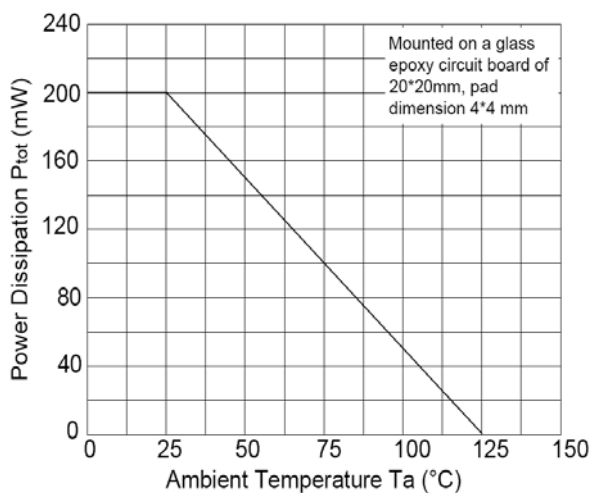


FIG.2 - TOTAL CAPACITANCE VS.
REVERSE VOLTAGE

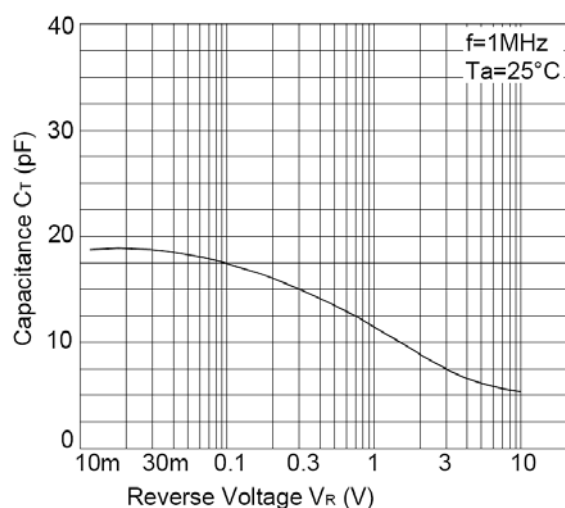


FIG.3 - FORWARD CURRENT VS.
FORWARD VOLTAGE

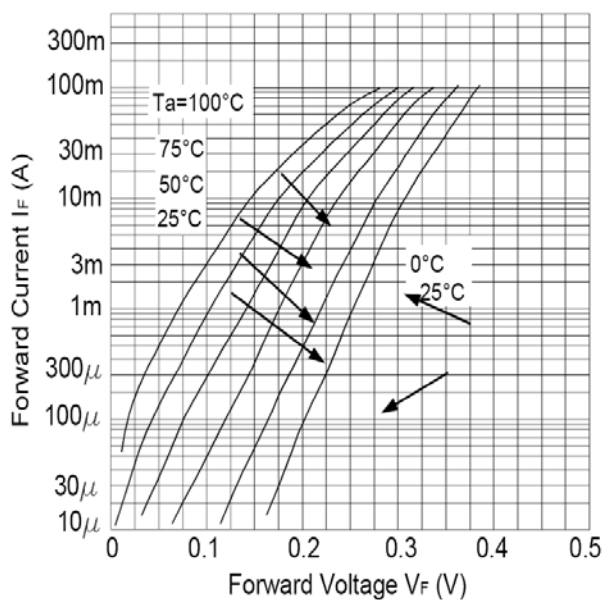


FIG.4 - REVERES CURRENT VS.
REVERES VOLTAGE

